

CVD Graphene on Cu foil

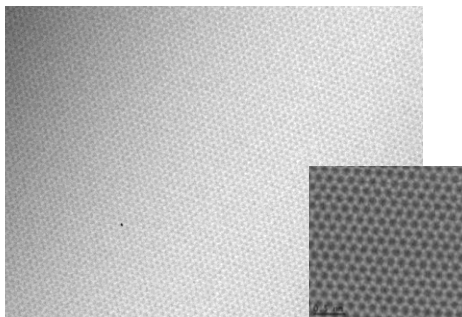


Ultra-Clean Graphene on SiO₂/Si Wafer



Product Size	Up to 90 x 90 mm ² (Max)
Film Morphology	Continuous Monolayer (>95%)
Sheet Resistance	Av. < 250~400 Ω/sq
Mobility	>3500 cm ² /Vs (Max. 17,000 cm ² /Vs)
Transmittance	>97%
Substrate	SiO ₂ (300nm)/Si wafer (Standard)
Domain Size	10-20 μm

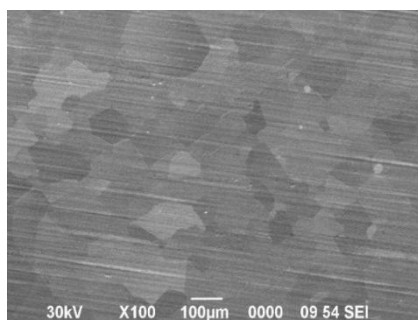
High-Resolution TEM Images



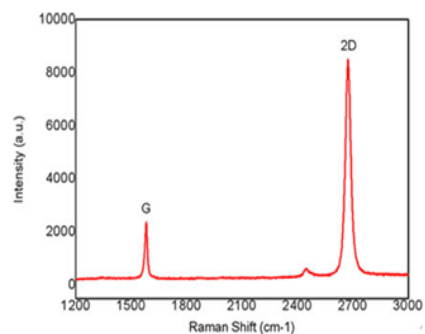
Substrate specifications

Orientation	<100>
Thickness	525±25 μm
Oxide Thickness	300nm
Type/Dopant	P/Boron
Resistivity	Resistivity

SEM Image of Graphene on Cu

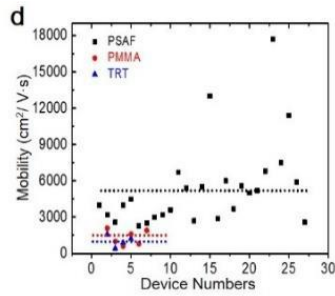
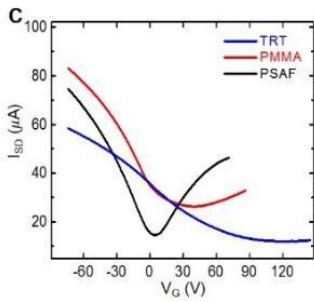


Raman Spectrum

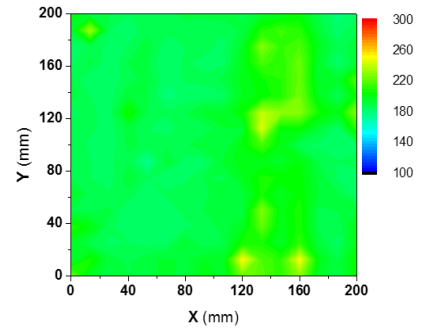




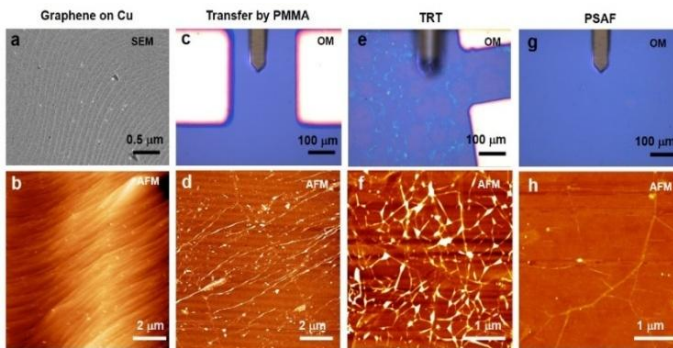
Electrical Properties



Sheet Resistance Uniformity



Ultra-Clean Transfer by Pressure Sensitive Adhesive Films



Reference

- (1) S. Kim *et al.* Ultra-Clean Patterned Transfer of Single-Layer Graphene by Recyclable Pressure Sensitive Adhesive Films. *Nano Lett.* (accepted).
- (2) S. Bae*, H. Kim* *et al.* Roll-to-roll production of 30 inch graphene films for transparent electrodes *Nature Nanotech.* **5**, 574 (2010).